The optical instabilities and blinking phenomena in the emission of InGaN quantum wells

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Recent advances in studies for InGaN/GaN have led to highbrightness green and blue light emitting diodes (LED). These wide band gap materials are currently used for many applications, for example full color displays, white (RGB) light sources or for the creation of shorter wavelength devices for optical data storage.

In this presentation, we will report our observations of intriguing optical instability (blinking phenomenon) in the photoluminescence of InGaN single quantum well devices. Similar fluores-cence blinking has been observed in three InP and GaAs, however the phenomenon is difficult to be explained in our case where the photoluminescence is generated in a system that is quantum confined only in a single direction (quantum well).



Excitation start

wavelength (nm) 3CCD Camera Microscope





Conclusions

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- We detected intermittency in PL fluorescence in GaN/InGaN sample
- We found dependence with Indium concentration, Excitation wavelength, excitation power, temperature
- Blinking is not a random process, it is not pure chaos.
- We found several domains that show **autocorrelation**.
- There is **correlation** between distant blinking domain.
- Correlation depends on **time lag**, suggesting space drift

- We found new spatial structures in the crystal that manifest themselves only in the blinking phenomenon.



300K



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